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NDS9945

Dual N-Channel Enhancement Mode Field Effect Transistor

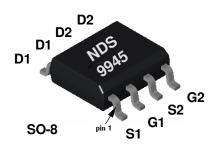
General Description

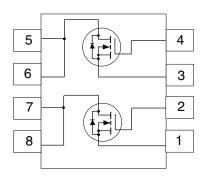
SO-8 N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to provide superior switching performance and minimize on-state resistance. These devices are particularly suited for low voltage applications such as disk drive motor control, battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- $\begin{tabular}{ll} \blacksquare & 3.5 \ A, \ 60 \ V. \ $R_{\rm DS(ON)} = 0.100 \ \Omega \ @ \ V_{\rm GS} = 10 \ V, \\ R_{\rm DS(ON)} = 0.200 \ \Omega \ @ \ V_{\rm GS} = 4.5 \ V. \end{tabular}$
- High density cell design for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.
- Dual MOSFET in surface mount package.







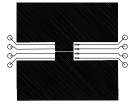
Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$ unless other wise noted

Symbol	Parameter	NDS9945	Units
V _{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	±20	V
D	Drain Current - Continuous (Note 1a)	3.5	А
	- Pulsed	10	
P_{D}	Power Dissipation for Dual Operation	2	W
	Power Dissipation for Single Operation (Note 1a)	1.6	
	(Note 1b)	1	
	(Note 1c)	0.9	
T_J , T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
THERMA	L CHARACTERISTICS		•
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R _{euc}	Thermal Resistance, Junction-to-Case (Note 1)	40	°C/W

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		60			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C			60		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, \ V_{GS} = 0 \text{ V}$				1	μΑ
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
GSSR	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V				-100	nA
ON CHARA	CTERISTICS (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		1	1.7	3	V
			T _J =125°C	0.7		2.2	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$			0.076	0.1	Ω
			T _J =125°C		0.124	0.18	
		$V_{GS} = 4.5 \text{ V}, I_D = 2.5 \text{ A}$			0.103	0.2	
			T _J =125°C		0.166	0.3	
D(ON)	On-State Drain Current	$V_{GS} = 10 \text{ V}, \ V_{DS} = 10 \text{ V}$		10			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 3.5 \text{ A}$			5.3		S
DYNAMIC (CH ARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			345		pF
C _{oss}	Output Capacitance				110		pF
C _{rss}	Reverse Transfer Capacitance				25		pF
SWITCHING	CHARACTERISTICS (Note 2)						
D(on)	Turn - On Delay Time	$V_{DS} = 30 \text{ V}, \ I_{D} = 1 \text{ A}$			5	25	ns
ţ,	Turn - On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$			7.5	30	
D(off)	Turn - Off Delay Time				20	50	
ţ,	Turn - Off Fall Time				7	40	
Q _g	Total Gate Charge	$V_{DS} = 30 \text{ V}, I_{D} = 3.5 \text{ A},$			12.9	30	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V			1.7		
Q_{gd}	Gate-Drain Charge				3.2		
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MA	XIMUM RATINGS					
S	Maximum Continuous Drain-Source Diode F	Forward Current				1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \ I_S = 1.3 \text{ A} \ \text{(Note 2)}$			0.8	1.2	V
rr	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_F = 1.3 \text{ A},$			40		ns
I _{rr}	Reverse Recovery Current	$dl_F/dt = 100 A/\mu s$			1.5		Α

Notes:

1. R_{BA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a. 78°C/W on a 0.5 in² pad of 2oz copper.





Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

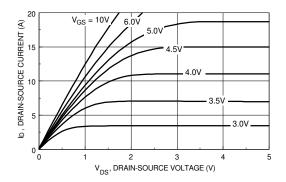


Figure 1. On-Region Characteristics.

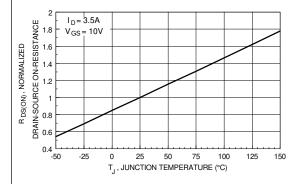


Figure 3. On-Resistance Variation With Temperature.

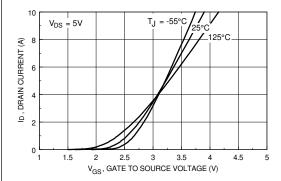


Figure 5 . Transfer Characteristics.

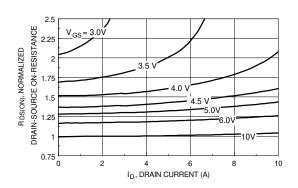


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

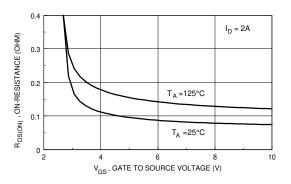


Figure 4. On Resistance Variation with Gate-to-Source Voltage.

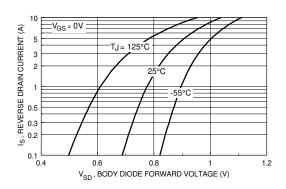
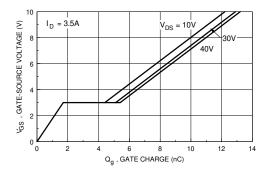


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics (continued)



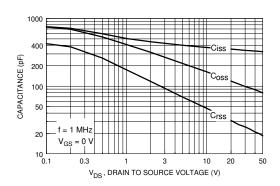
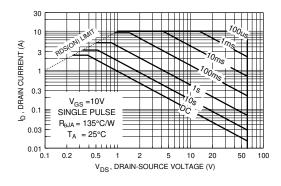


Figure 7. Gate Charge Characteristics.





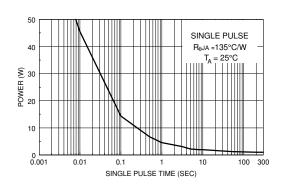


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

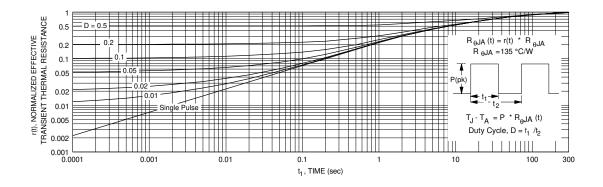


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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